

IGBT

High speed 5 FAST IGBT in TRENCHSTOP™ 5 technology

IGW50N65F5

650V IGBT high speed switching series fifth generation

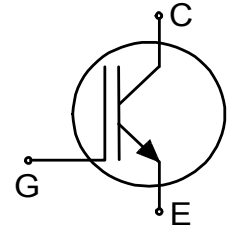
Data sheet

Industrial Power Control

High speed 5 FAST IGBT in TRENCHSTOP™ 5 technology

Features and Benefits:

- High speed F5 technology offering
- Best-in-Class efficiency in hard switching and resonant topologies
 - 650V breakdown voltage
 - Low Q_G
 - Ideal fit with SiC Schottky Diode in boost converters
 - Maximum junction temperature 175°C
 - Qualified according to JEDEC for target applications
 - Pb-free lead plating; RoHS compliant
 - Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

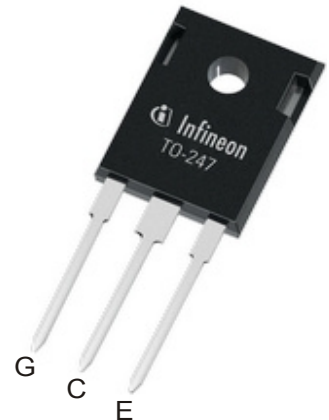


Applications:

- Solar converters
- Uninterruptible power supplies
- Welding converters
- Mid to high range switching frequency converters

Package pin definition:

- Pin 1 - gate
- Pin 2 & backside - collector
- Pin 3 - emitter



Key Performance and Package Parameters

| Type | V_{CE} | I_C | $V_{CEsat}, T_{vj}=25^\circ C$ | T_{vjmax} | Marking | Package |
|------------|----------|-------|--------------------------------|-------------|---------|------------|
| IGW50N65F5 | 650V | 50A | 1.6V | 175°C | G50EF5 | PG-TO247-3 |



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Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

| Parameter | Symbol | Value | Unit |
|---|-------------|----------------------|------------------|
| Collector-emitter voltage | V_{CE} | 650 | V |
| DC collector current, limited by T_{vjmax} $T_C = 25^\circ\text{C}$ value limited by bondwire $T_C = 100^\circ\text{C}$ | I_C | 80.0 56.0 | A |
| Pulsed collector current, t_p limited by T_{vjmax} | I_{Cpuls} | 150.0 | A |
| Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^\circ\text{C}$ | - | 150.0 | A |
| Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$) | V_{GE} | ± 20 ± 30 | V |
| Power dissipation $T_C = 25^\circ\text{C}$ Power dissipation $T_C = 100^\circ\text{C}$ | P_{tot} | 305.0 152.5 | W |
| Operating junction temperature | T_{vj} | -40...+175 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55...+150 | $^\circ\text{C}$ |
| Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s | | 260 | $^\circ\text{C}$ |
| Mounting torque, M3 screw Maximum of mounting processes: 3 | M | 0.6 | Nm |

Thermal Resistance

| Parameter | Symbol | Conditions | Max. Value | Unit |
|---|---------------|------------|------------|------|
| Characteristic | | | | |
| IGBT thermal resistance, junction - case | $R_{th(j-c)}$ | | 0.50 | K/W |
| Thermal resistance junction - ambient | $R_{th(j-a)}$ | | 40 | K/W |

Electrical Characteristic, at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|---------------|---|-------------|----------------------|----------------|---------------|
| | | | min. | typ. | max. | |
| Static Characteristic | | | | | | |
| Collector-emitter breakdown voltage | $V_{(BR)CES}$ | $V_{GE} = 0\text{V}$, $I_C = 0.20\text{mA}$ | 650 | - | - | V |
| Collector-emitter saturation voltage | V_{CEsat} | $V_{GE} = 15.0\text{V}$, $I_C = 50.0\text{A}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 125^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$ | - - - | 1.60 1.80 1.90 | 2.10 - - | V |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | $I_C = 0.50\text{mA}$, $V_{CE} = V_{GE}$ | 3.2 | 4.0 | 4.8 | V |
| Zero gate voltage collector current | I_{CES} | $V_{CE} = 650\text{V}$, $V_{GE} = 0\text{V}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$ | - - | - - | 40.0 2000.0 | μA |
| Gate-emitter leakage current | I_{GES} | $V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$ | - | - | 100 | nA |
| Transconductance | g_{fs} | $V_{CE} = 20\text{V}$, $I_C = 50.0\text{A}$ | - | 62.0 | - | S |

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--|-----------|---|-------|-------|------|------|
| | | | min. | typ. | max. | |
| Dynamic Characteristic | | | | | | |
| Input capacitance | C_{ies} | $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$ | - | 3000 | - | pF |
| Output capacitance | C_{oes} | | - | 50 | - | |
| Reverse transfer capacitance | C_{res} | | - | 11 | - | |
| Gate charge | Q_G | $V_{CC} = 520\text{V}, I_C = 50.0\text{A}, V_{GE} = 15\text{V}$ | - | 120.0 | - | nC |
| Internal emitter inductance measured 5mm (0.197 in.) from case | L_E | | - | 13.0 | - | nH |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

| | | | | | | |
|------------------------|--------------|---|---|------|---|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 25^{\circ}\text{C}, V_{CC} = 400\text{V}, I_C = 25.0\text{A}, V_{GE} = 0.0/15.0\text{V}, R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega, L\sigma = 30\text{nH}, C\sigma = 30\text{pF}$ Energy losses include "tail" and diode reverse recovery. | - | 21 | - | ns |
| Rise time | t_r | | - | 15 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 175 | - | ns |
| Fall time | t_f | | - | 18 | - | ns |
| Turn-on energy | E_{on} | | - | 0.49 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.16 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.65 | - | mJ |
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 25^{\circ}\text{C}, V_{CC} = 400\text{V}, I_C = 6.0\text{A}, V_{GE} = 0.0/15.0\text{V}, R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega, L\sigma = 30\text{nH}, C\sigma = 30\text{pF}$ Energy losses include "tail" and diode reverse recovery. | - | 19 | - | ns |
| Rise time | t_r | | - | 4 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 195 | - | ns |
| Fall time | t_f | | - | 10 | - | ns |
| Turn-on energy | E_{on} | | - | 0.11 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.04 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.15 | - | mJ |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|--|--------------|--|-------|------|------|------|
| | | | min. | typ. | max. | |
| IGBT Characteristic, at $T_{vj} = 150^{\circ}\text{C}$ | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 150^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 25.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 12.0\Omega$, $R_{G(off)} = 12.0\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 20 | - | ns |
| Rise time | t_r | | - | 15 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 202 | - | ns |
| Fall time | t_f | | - | 3 | - | ns |
| Turn-on energy | E_{on} | | - | 0.68 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.21 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.89 | - | mJ |
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 150^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 6.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 12.0\Omega$, $R_{G(off)} = 12.0\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 18 | - | ns |
| Rise time | t_r | | - | 5 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 245 | - | ns |
| Fall time | t_f | | - | 12 | - | ns |
| Turn-on energy | E_{on} | | - | 0.18 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.06 | - | mJ |
| Total switching energy | E_{ts} | | - | 0.24 | - | mJ |

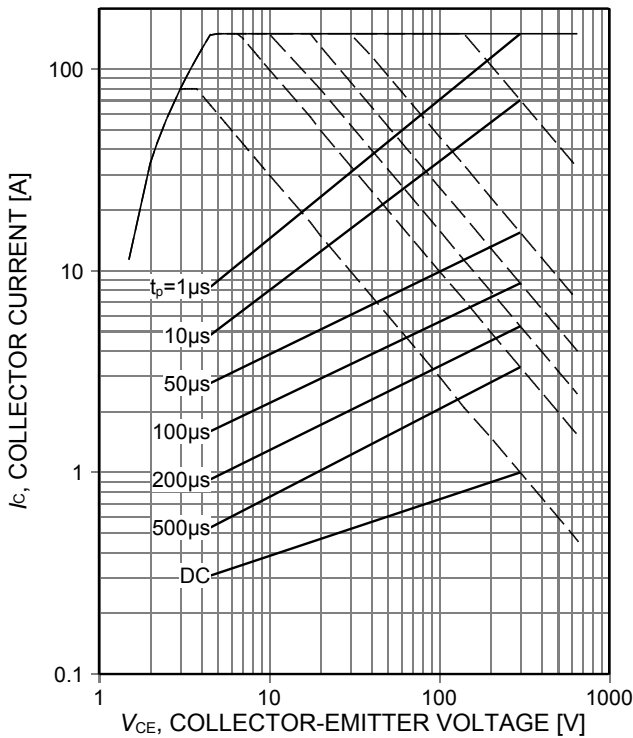


Figure 1. **Forward bias safe operating area**
 ($D=0$, $T_C=25^\circ\text{C}$, $T_{vj}\leq 175^\circ\text{C}$; $V_{GE}=15\text{V}$.
 Recommended use at $V_{GE}\geq 7.5\text{V}$)

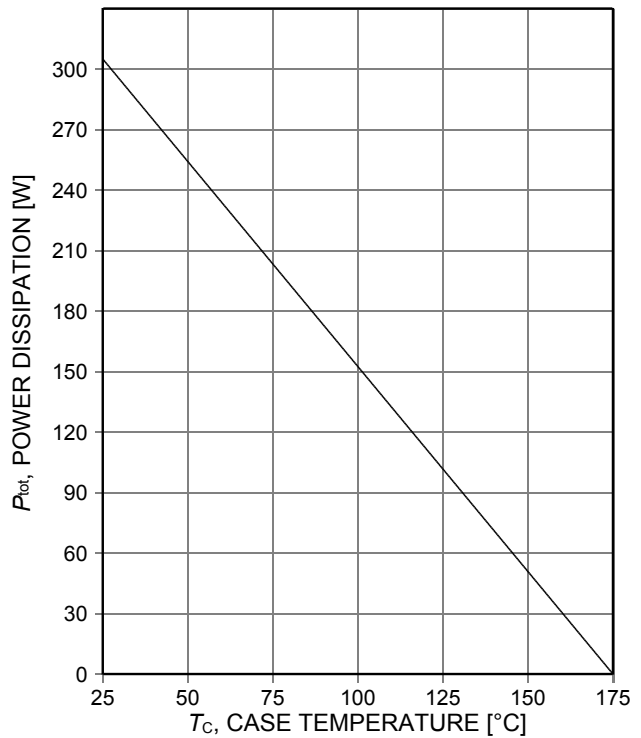


Figure 2. **Power dissipation as a function of case temperature**
 ($T_{vj}\leq 175^\circ\text{C}$)

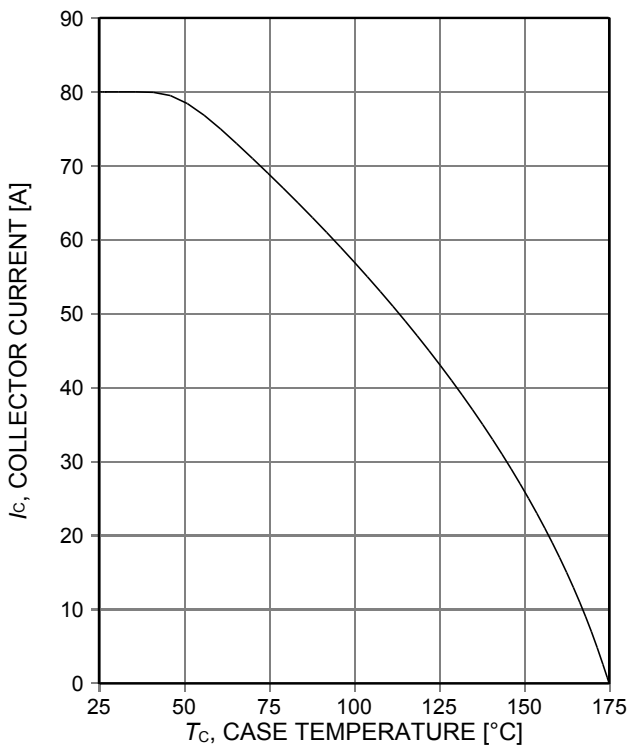


Figure 3. **Collector current as a function of case temperature**
 ($V_{GE}\geq 15\text{V}$, $T_{vj}\leq 175^\circ\text{C}$)

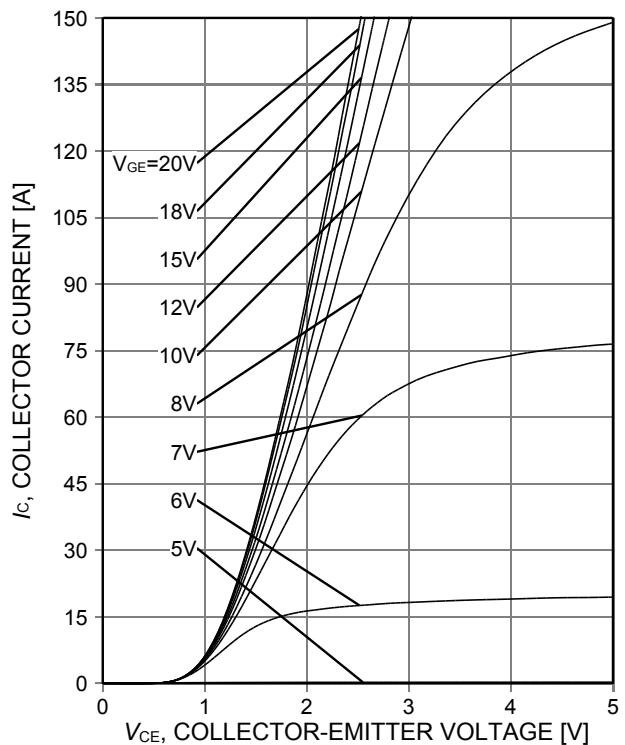


Figure 4. **Typical output characteristic**
 ($T_{vj}=25^\circ\text{C}$)

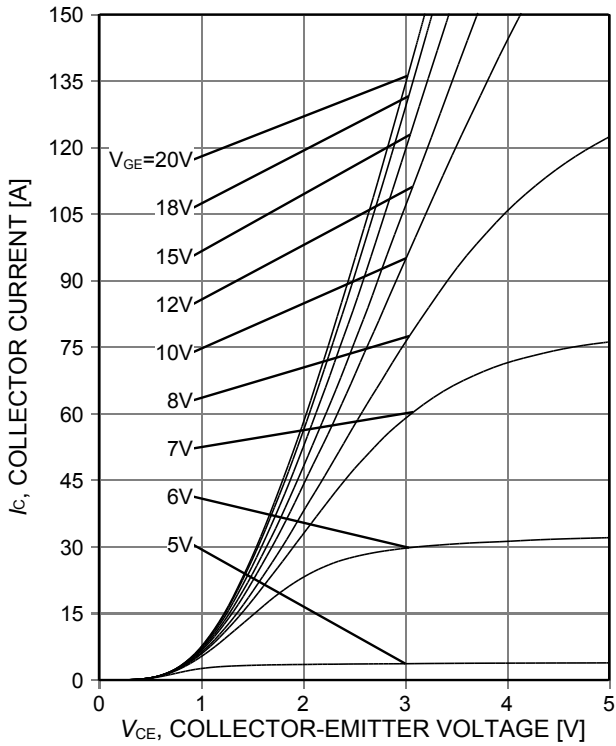


Figure 5. Typical output characteristic ($T_{vj}=150^{\circ}\text{C}$)

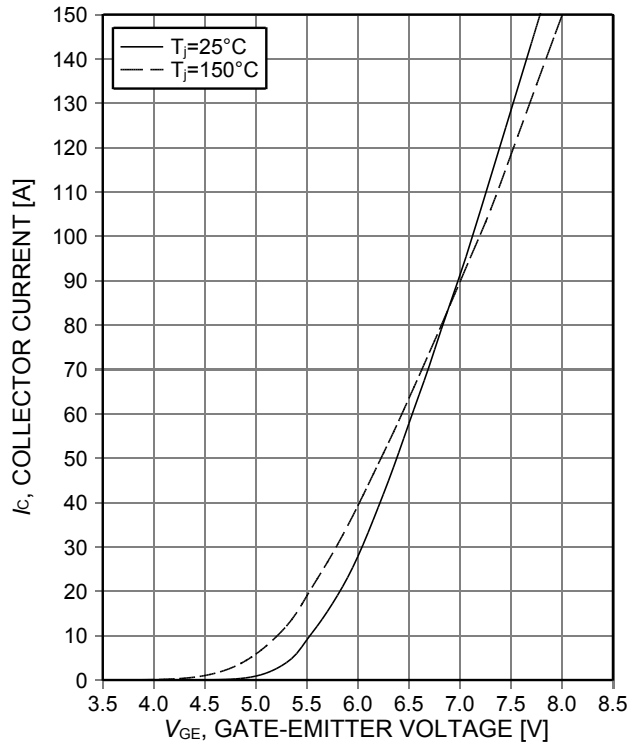


Figure 6. Typical transfer characteristic ($V_{CE}=20\text{V}$)

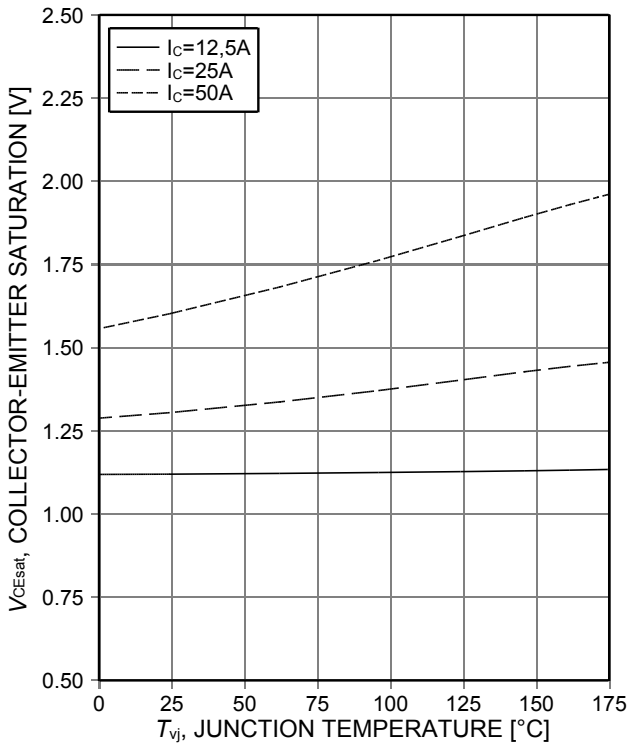


Figure 7. Typical collector-emitter saturation voltage as a function of junction temperature ($V_{GE}=15\text{V}$)

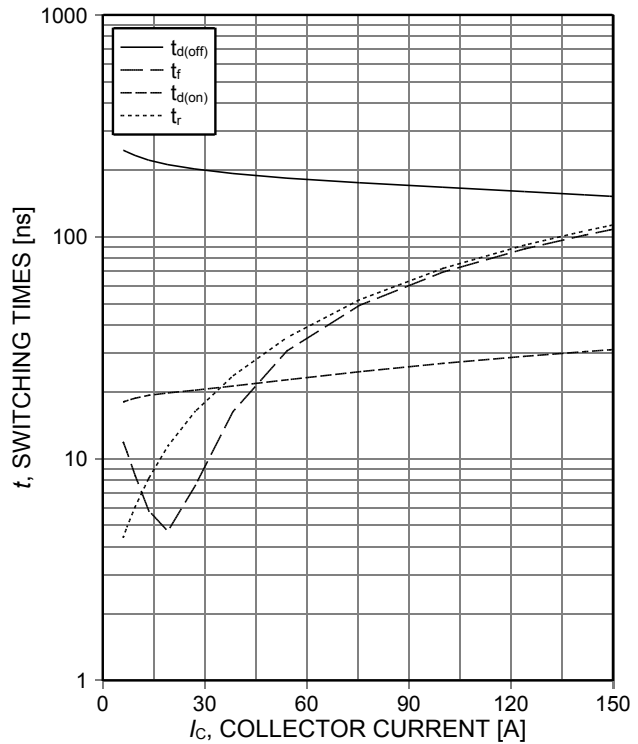


Figure 8. Typical switching times as a function of collector current (inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

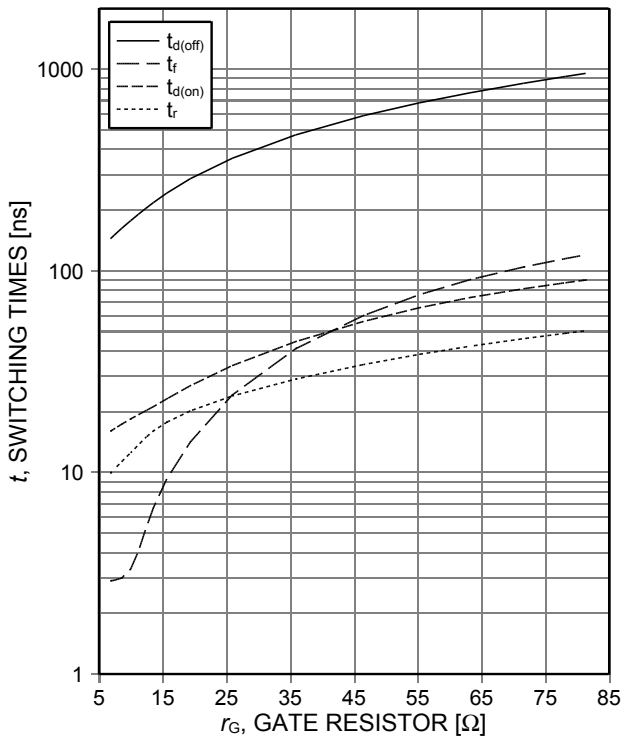


Figure 9. **Typical switching times as a function of gate resistor**
 (inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=25\text{A}$, Dynamic test circuit in Figure E)

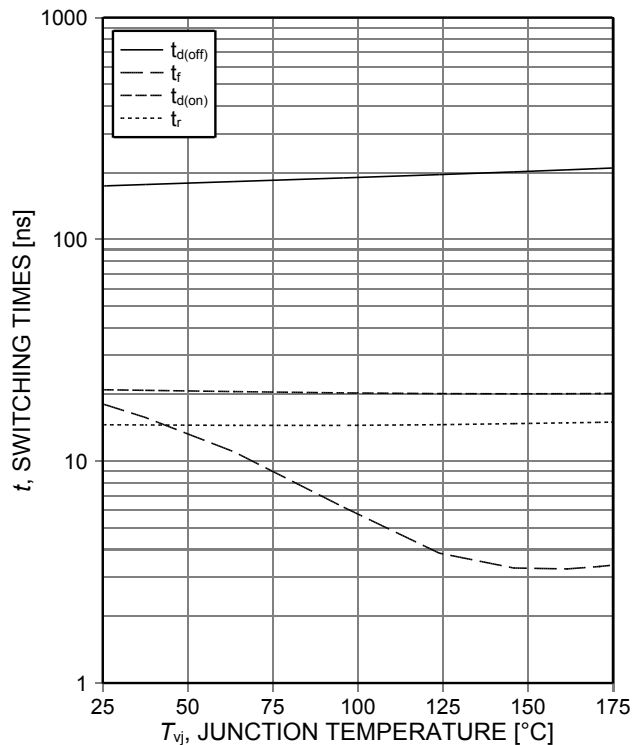


Figure 10. **Typical switching times as a function of junction temperature**
 (inductive load, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=25\text{A}$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

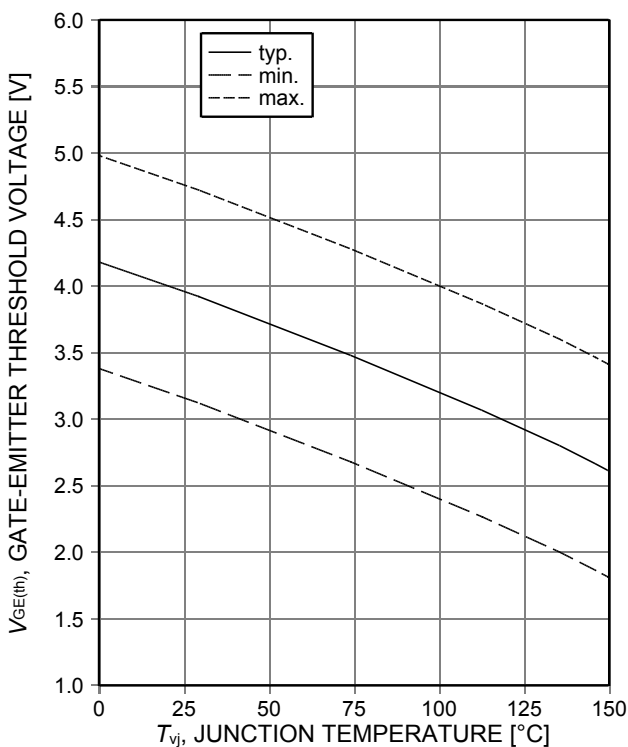


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**
 ($I_C=0.5\text{mA}$)

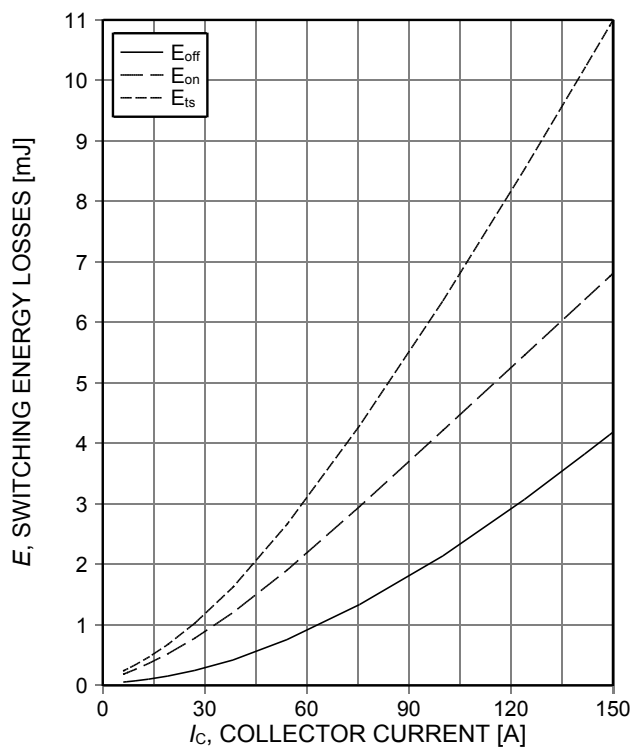


Figure 12. **Typical switching energy losses as a function of collector current**
 (inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

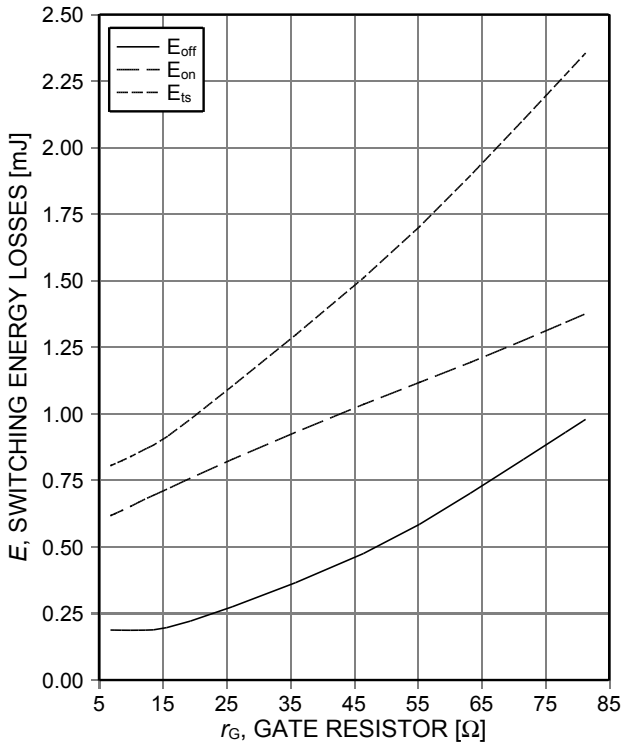


Figure 13. Typical switching energy losses as a function of gate resistor (inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=25\text{A}$, Dynamic test circuit in Figure E)

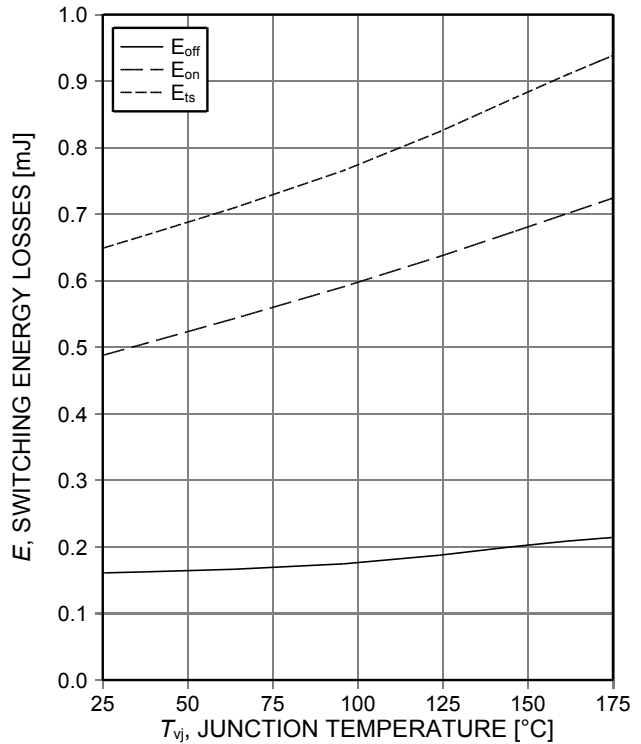


Figure 14. Typical switching energy losses as a function of junction temperature (inductive load, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=25\text{A}$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

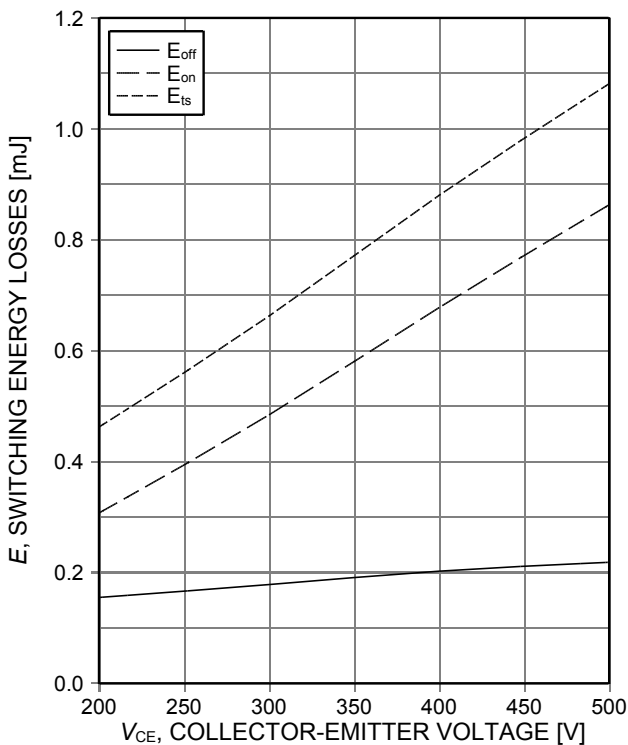


Figure 15. Typical switching energy losses as a function of collector emitter voltage (inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{GE}=15/0\text{V}$, $I_C=25\text{A}$, $r_G=12\Omega$, Dynamic test circuit in Figure E)

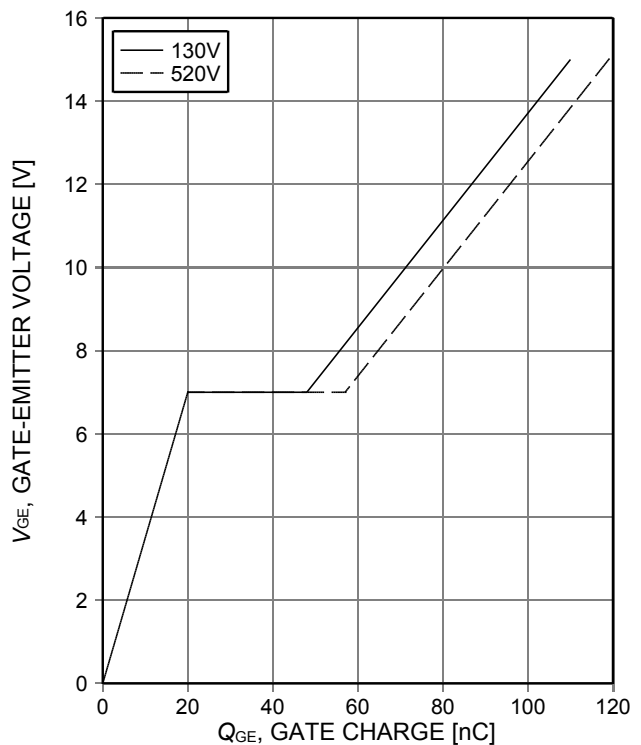


Figure 16. Typical gate charge ($I_C=50\text{A}$)

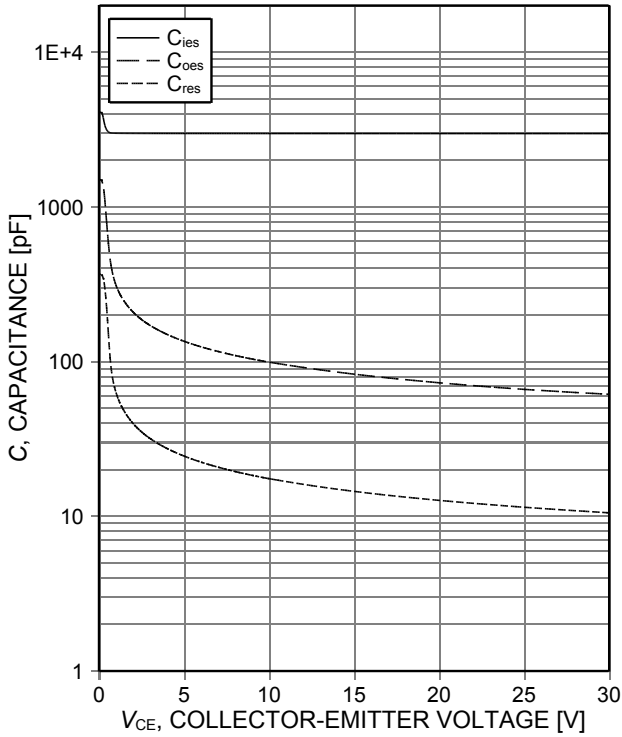


Figure 17. Typical capacitance as a function of collector-emitter voltage ($V_{GE}=0V$, $f=1MHz$)

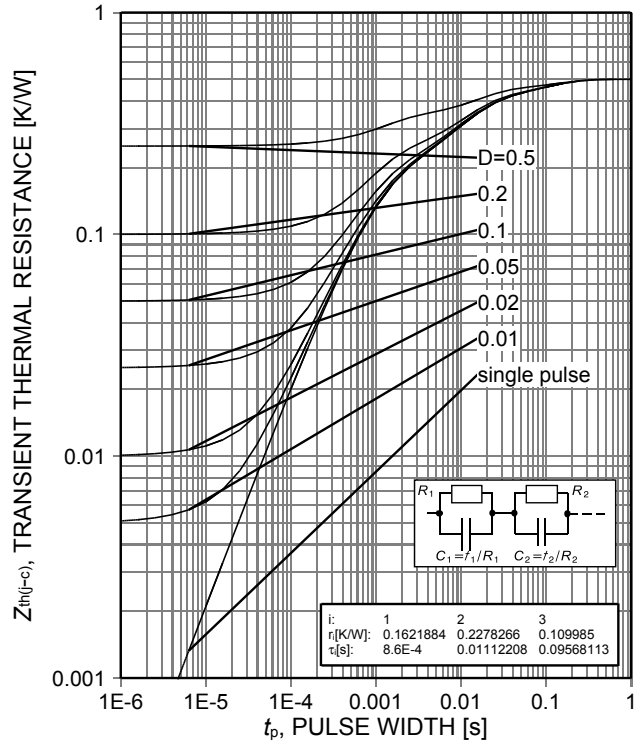
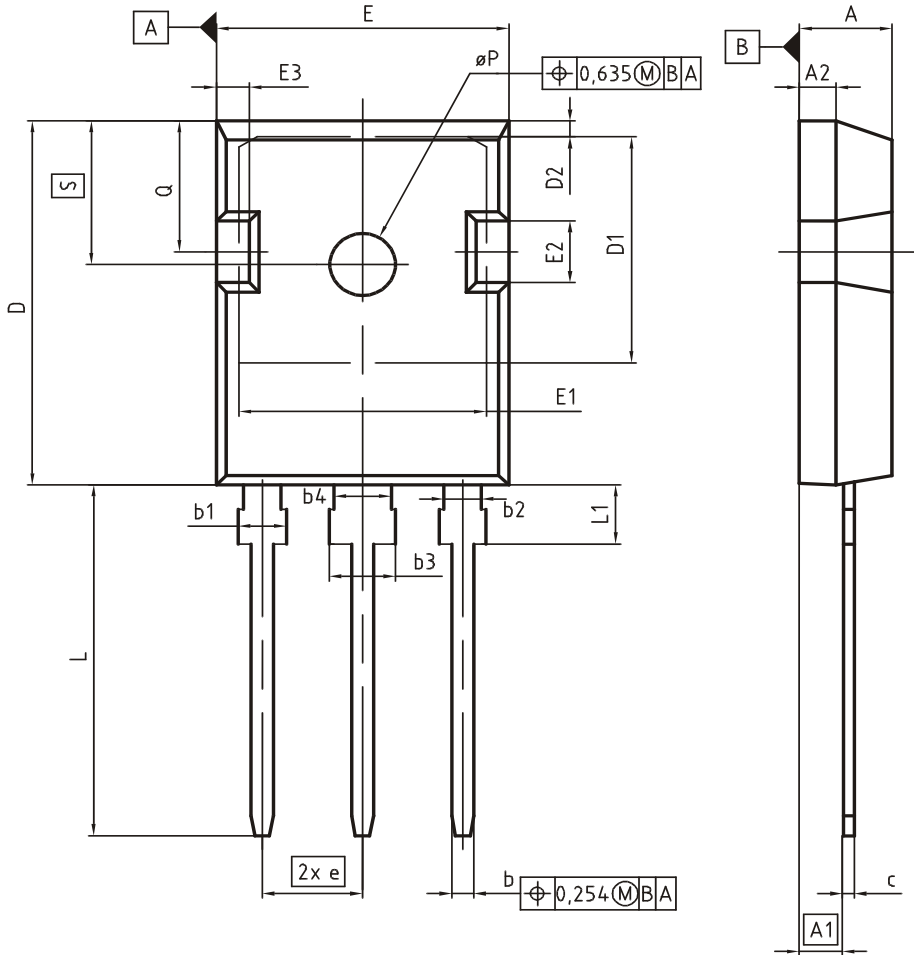


Figure 18. IGBT transient thermal resistance ($D=t_p/T$)

Package Drawing PG-TO247-3



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.83 | 5.21 | 0.190 | 0.205 |
| A1 | 2.27 | 2.54 | 0.089 | 0.100 |
| A2 | 1.85 | 2.16 | 0.073 | 0.085 |
| b | 1.07 | 1.33 | 0.042 | 0.052 |
| b1 | 1.90 | 2.41 | 0.075 | 0.095 |
| b2 | 1.90 | 2.16 | 0.075 | 0.085 |
| b3 | 2.87 | 3.38 | 0.113 | 0.133 |
| b4 | 2.87 | 3.13 | 0.113 | 0.123 |
| c | 0.55 | 0.68 | 0.022 | 0.027 |
| D | 20.80 | 21.10 | 0.819 | 0.831 |
| D1 | 16.25 | 17.65 | 0.640 | 0.695 |
| D2 | 0.95 | 1.35 | 0.037 | 0.053 |
| E | 15.70 | 16.13 | 0.618 | 0.635 |
| E1 | 13.10 | 14.15 | 0.516 | 0.557 |
| E2 | 3.68 | 5.10 | 0.145 | 0.201 |
| E3 | 1.00 | 2.60 | 0.039 | 0.102 |
| e | 5.44 (BSC) | | 0.214 (BSC) | |
| N | 3 | | 3 | |
| L | 19.80 | 20.32 | 0.780 | 0.800 |
| L1 | 4.10 | 4.47 | 0.161 | 0.176 |
| øP | 3.50 | 3.70 | 0.138 | 0.146 |
| Q | 5.49 | 6.00 | 0.216 | 0.236 |
| S | 6.04 | 6.30 | 0.238 | 0.248 |

DOCUMENT NO.
Z8B00003327

SCALE

EUROPEAN PROJECTION

ISSUE DATE
09-07-2010

REVISION
05

Testing Conditions

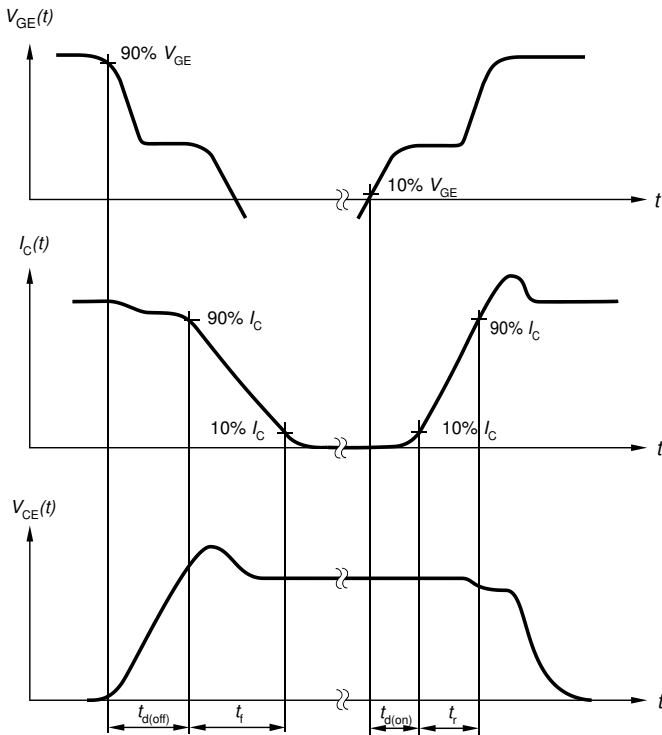


Figure A. Definition of switching times

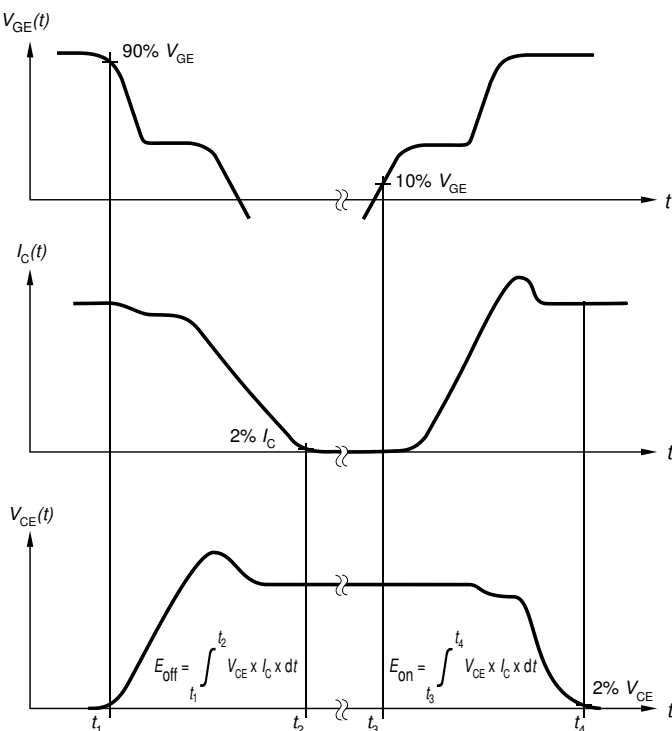


Figure B. Definition of switching losses

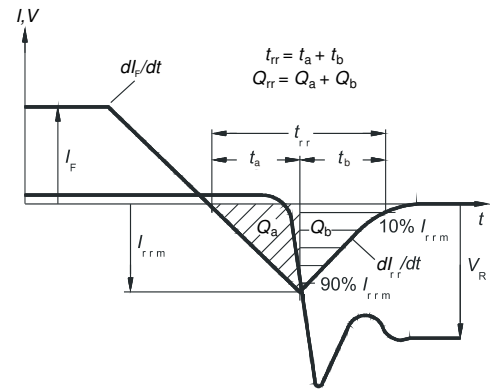


Figure C. Definition of diode switching characteristics

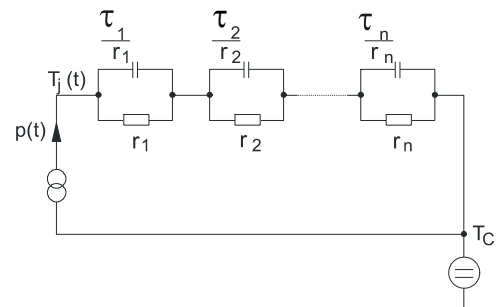


Figure D. Thermal equivalent circuit

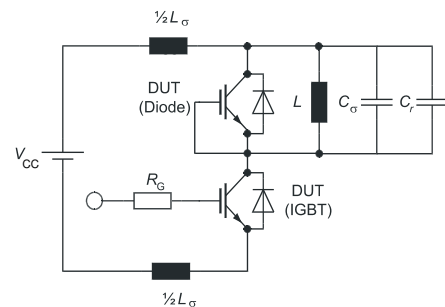


Figure E. Dynamic test circuit
Parasitic inductance L_{σ} ,
parasitic capacitor C_{σ} ,
relief capacitor C_r ,
(only for ZVT switching)

Revision History

IGW50N65F5

Revision: 2015-05-04, Rev. 2.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 1.1 | 2012-11-09 | Preliminary data sheet |
| 1.2 | 2013-12-16 | New Marking Pattern |
| 2.1 | 2015-05-04 | Final data sheet |

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Any information within this document that you feel is wrong, unclear or missing at all?

Your feedback will help us to continuously improve the quality of this document.

Please send your proposal (including a reference to this document) to: erratum@infineon.com

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The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.



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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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